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An abrupt change in transport dynamics across the topological phase transition in the $(Bi_{1-x}In_x)_2Se_3$ system

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We have utilized time-domain terahertz (THz) spectroscopy to investigate the low frequency optical conductivity in $(Bi_{1-x}In_x)_2Se_3$ through its topological phase transition from the pure ($x = 0$) compound to the topologically trivial strongly insulating material ($x > 0.25$). We find a number of large changes in the spectral properties with indium (In) substitution. The thickness independent Drude peak shows only minor broadening at low In substitutions. However, above $x \sim 0.05$ we observe a sudden collapse in the transport lifetime. This substitution level closely coincides with a maximum in the mid-infrared (MIR) absorption coefficient which can be identified with the substitution level where the band gap closes, the band structure inverts, and hence the topological class changes. We therefore associate the collapse in the transport lifetime with the loss of topological protection of surface states as the system enters the topologically trivial phase. The role of finite size effects in this transition is also discussed.

Topological insulators (TIs) are new states of matter characterized by an "inverted" band structure [1–3] driven by strong spin-orbit (SO) coupling. Their topological nature is determined by the parity of the valence-band wave functions, which can be quantified by 4 Z_2 topological invariants.[4–6] Fu and Kane have shown that for inversion symmetric crystals it is possible to evaluate these invariants directly with knowledge of the parity of Bloch wave functions for the occupied electronic states at high symmetry points in the Brillouin zone.[7] The fact that distinct Z_2 invariants exist means that these materials cannot be adiabatically connected to conventional band insulators. Topological insulators are predicted to have a variety of unusual properties including robust topologically protected surface states (SS) with a massless Dirac spectrum.

As TIs are a distinct state of matter, it is of particular interest to study the quantum phase transition to a non-topological state. Although Fu and Kane's argument is formulated for inversion symmetric systems, a material's topological classification does not require inversion or translation symmetry.[7] Therefore the expectation is that the alloying of known TIs with lighter elements can cause the bulk band gap Δ to close and invert at a quantum critical point where the topological class changes. The obvious substitution of the lighter element sulphur (S) onto the selenium (Se) site of the much studied Bi_2Se_3 compound turns out to be inappropriate to study this transition. Although S lies in the same column of the periodic table as Se, the crystal structure of Bi_2S_3 is orthorhombic with space group V_h^{16} (*Pbnm*) with a twenty atom unit cell,[8, 9] which contrasts with the rhomehedral structure of Bi_2Se_3 that has a symmetry D_{3d}^5 ($R\bar{3}m$) with 5 atoms per unit cell. This has led researchers to investigate the thallium-based ternary chalcogenide alloy $TlBi(S_{1-x}Se_x)_2$ that does maintain the same crystal structure throughout the $TlBiSe_2 \rightarrow TlBiS_2$ series.[10–12] There, substitution of the lighter sulfur drives the system towards $TlBiS_2$ which is a topologically trivial insulator. It has been found that bulk band gap inversion happens around $x = 0.5$, with a subsequent loss of the topological surface states. In one study,[11, 12] it was observed, quite contrary to expectations, that the SS opens up a gap at the Dirac point at $x \sim 0.9$ despite the fact that the two spin species are not found on the surface until the point where the TI/non-TI transition occurs. This "mass acquisition" in a non-spin degenerate band is as of yet unexplained.

To investigate the transition, clarify this phenomenon, it would be interesting to investigate this physics in the most studied material class of Bi_2Se_3, especially in transport experiments. In this regard, it was recently pointed out that indium (In) substitutes for bismuth to form a solid solution in Bi_2Se_3 and that the end member In_2Se_3 of the $(Bi_{1-x}In_x)_2Se_3$ series shares the common rhombohedral D_{3d}^5 structure with Bi_2Se_3. [13] Indium substitution should be particularly interesting as it is expected to have a large effect on the electronic properties of TIs because it substitutes for Bi, the heaviest element in Bi_2Se_3, and is therefore a very sensitive way to tune SO coupling. In_2Se_3 is a band insulator without band inversion. Starting from pure Bi_2Se_3, with increasing In substitution, a transition from TI to trivial insulator is expected and gives rise to a change in the Z_2 invariant because of loss of band inversion. We should note that, because of natural n-type bulk doping,[14, 15] Bi_2Se_3 may be better referred to as a topological metal. In a DC transport and ARPES investigation [13] it was inferred that with In substitution a phase transition from topological metal to normal metal occurs between $x = 0.03 - 0.07$, and a metal-insulator transition around $x = 0.15$ to an disordered insulator with variable-range-hopping type transport. The system becomes a band insulator above $x = 0.25$. It is important to emphasize that indium was not found to function primarily as dopant, but instead appears to modify the spin-orbit coupling while maintaining the same lattice structure.[13]

In this work we have utilized time-domain THz spectroscopy (TDTS) to investigate the low frequency optical conductivity in a series of In substituted Bi_2Se_3 thin films from the pure compound all the way to the topologically trivial strongly insulating material. We find a number of large changes in the spectral properties with In substitution, which can be associated with the collapse of the topologically robust surface state, and upon further In substitution, with the development of the trivially insulating state. The precise substitution level can be confirmed as the low frequency infrared active phonon moves strongly to higher frequencies in a linear fashion with substitution of indium. At low frequencies, the Drude peak, which we have previously shown to exhibit thickness independent transport and identified as being primarily due to the topological surface states (TSS),[16, 17] shows only minor broadening at low In substitutions. However for substitutions above $x = 0.05$ we find a sudden and dramatic collapse in the Drude transport lifetime. We can correlate these changes with a peak in the MIR absorption that occurs around $x = 0.06$. The substitution range where this peak occurs can be associated with the closing of the bulk band gap and a transition to a non-topological metalic state. Therefore we can attribute the enhanced scattering of the Drude component to the loss of topological protection of surface states upon entering into the non-topological regime.

Standard TDTS in a transmission geometry was performed with a custom home-built THz spectrometer. In this technique an almost single-cycle 1 picosecond pulse of light is transmitted through the sample. The complex transmission function that results from Fourier transforming the pulse and ratioing it to a Fourier transformed reference pulse can be directly inverted to give the complex conductance in the thin film limit.[16] TDTS turns out to be an ideal probe of the low frequency response of these materials with both the metallic Drude transport peak and the phonon peak observable in the experimental range. Thin films of Bi_2Se_3 of 64 quintuple layers (1QL$\sim$1nm) thickness were grown at Rutgers University by a molecular beam epitaxy (MBE) technique on 0.5 mm thick crystalline Al_2O_3 substrates. Details on growth can be found elsewhere.[18, 19] Indium was incorporated during the film deposition and the concentration can be controlled at better than the 1% level. Samples were sealed in vacuum and sent immediately to JHU. The total exposure time to atmosphere was less than 30 minutes . Low temperatures TDTS measurements began within 24 hours of their growth. The samples were mounted inside an optical helium flow cryostat and cooled down to 5K within an hour. Transmission measurements in the mid-infrared (MIR) region were performed with a Fourier transform infrared reflectivity (FTIR) spectrometer (Bruker Vertex 80) at room temperature in vacuum.

In Fig. 1, we show the real and imaginary conductance of a series of $(Bi_{1-x}In_x)_2Se_3$ films substituted from $x = 0$ to $x = 0.25$ at 5K in the THz frequency range. For $x = 0$ the spectra are characterized by a prominent low frequency Drude component, which we have previously shown as an almost entirely surface character and the low frequency phonon at $\sim$1.9 THz.[16] With increasing In concentration, the phonon mode broadens and its energy shifts dramatically in an almost linear fashion (see Fig. 3(c)) to higher frequency due to the lighter mass of indium. The Drude peak broadens only slightly up to $x = 0.04$ in a fashion expected due to the increased disorder. However for substitutions larger than x=0.05 the Drude peak broadens dramatically and the real part of the conductance becomes almost flat, indicating that the SS has undergone a significant change. For $x \geq 0.10$, conductance is a slowly increasing function of frequency ω consistent with a tendency towards charge localization. The residual conductance of $x = 0.10$ at low frequency indicates still some metallic behavior that can be confirmed from the electron pocket seen by angle resolved photoemission (ARPES) studies.[13] The nearly zero conductance of $x = 0.17$ and $x = 0.25$ at low frequency and correspondingly the imaginary conductance having a negative slope indicate insulating behavior for these concentration levels.

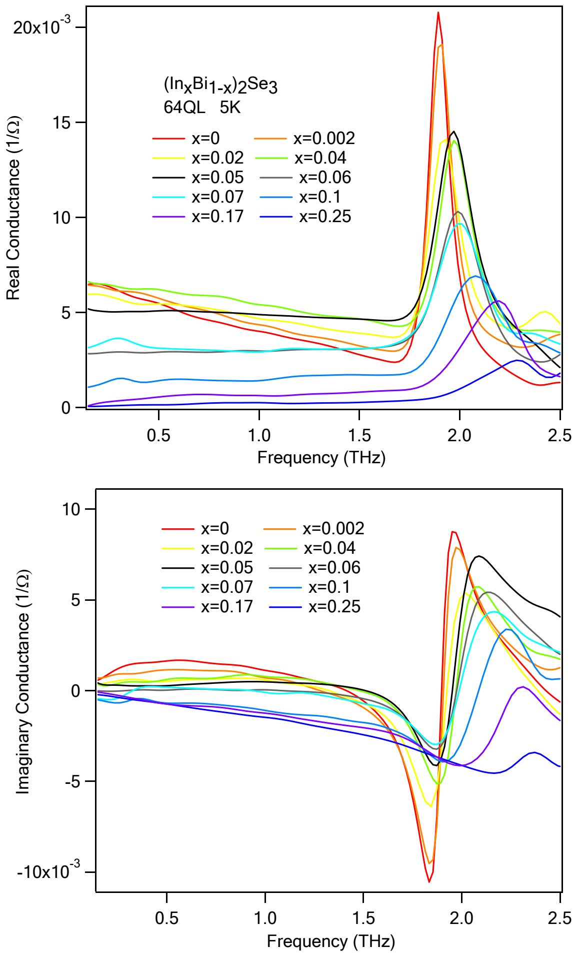

FIG. 1: (Color online) (a) Real and (b) Imaginary parts of the THz range sheet conductance for different indium concentration levels $(Bi_{1-x}In_x)_2Se_3$ of same thickness 64QL films at 5K.

In Fig. 2(a) we show the temperature and frequency dependence of the real condutance of pure Bi_2Se_3 film. The Drude peak broadens with increasing temperature, which is consis-

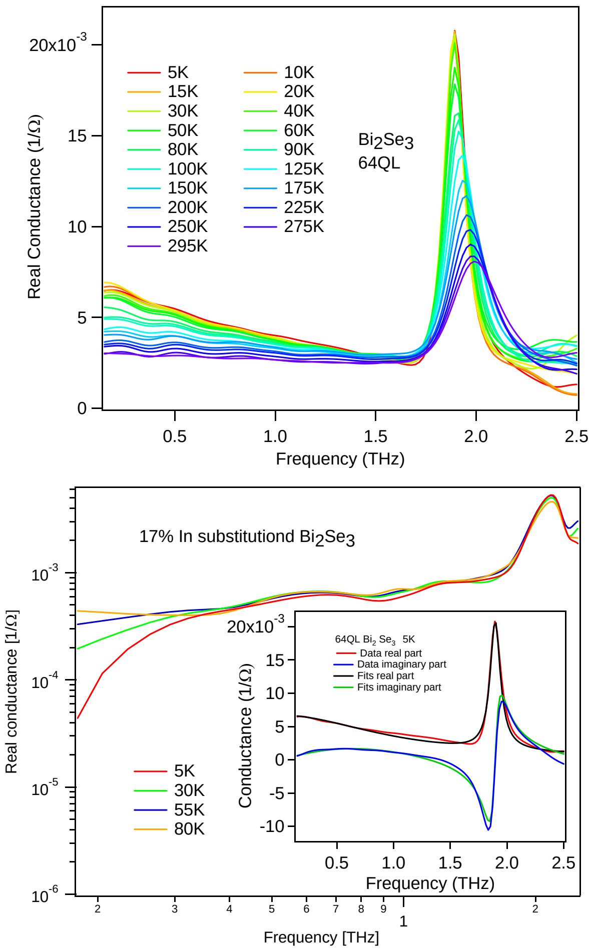

FIG. 2: (Color online) Temperature dependence of real conductance of (a) 0% and (b) 17% indium concentration. Insert: experimental data with fits for 64QL pure Bi_2Se_3 at 5K

tent with the expectation for conventional metallic transport. The phonon shifts to higher frequency by 97 GHz ($\sim$3 cm^{-1}) from 5 K to room temperature. As noted earlier, such a large phonon hardening is unusual without a structural transition nearby in configuration space.[20] Below 30K, the low frequency Drude peak has no notable temperature dependence and the Drude scattering rate is almost constant within our experimental accuracy. This, along with the fact that the DC resistance is constant below 30K,[19] shows that even in the pure sample transport is dominated by impurity scattering. In contrast, $(In_{0.17}Bi_{0.83})_2Se_3$ which is well into the topologically trivial regime shows increasing conductance as a function of frequency and the opposite temperature dependence at low frequency (Fig. 2(b)), indicating the formation of a localized insulating state. This indicates that a metal-insulator transition by disorder induced localization has occured, which agrees with DC transport data.[13] $\sigma_1(\omega)$ (conductance/thickness) typically shows a simple power-law behavior at low frequency ω in insulators with strong localization in the variable range hopping regime,[21] which interestingly is not exhibited in the measured spectral range in the present case.

To investigate the details of the substitution evolution through the nominal topological quantum phase transition, we fit the data to a Drude-Lorentz model. We include only a single Drude term (a Lorentzian centered at $\omega = 0$), a Drude-Lorentz term (which models the phonon) and a frequency independent real ϵ_∞ contribution to the dielectric constant (that accounts for the effect of higher energy excitations on the low frequency physics).[16, 17] As shown by the inset in Fig. 2(b), the fit with a single Drude term is excellent and no other channels arising from bulk or surface accumulated regions are necessary. The only possibilities to accommodate such channels are if these have scattering rates roughly coincident with the primary channel (which we consider unlikely), or more plausibly, if their scattering rates are so large as to make their contribution at low frequency small and featureless within the measured spectral range.

Consistent with our previous observation and our expectation due to increased impurity scattering, the Drude scattering rate increases smoothly up to $x = 0.04$ (Fig. 3(a)). At $x = 0.05$, the smooth trend suddenly changes and the scattering rate is enhanced dramatically. Just by In substitution alone, we would expect a continued smooth increase of the scattering rate. An extended Drude analysis reveals electron-phonon coupling and electron-electron interaction are weak in these materials.[22] Therefore, the sudden change across $x = 0.05$ indicates a transition occurring in the TSS.

We can correlate the sudden changes in the transport properties of the surface with the high-energy band structure by performing optical absorption measurements in the mid-infrared range, which are sensitive to the energy scale of the bulk band gap. In Fig. 3(d) we show that the MIR absorption coefficient at 0.31 eV (below bulk band gap for the $x = 0$ compound) shows a distinct peak near $x = 0.06$. We can associate such a peak with the closing of the bulk band gap. Despite the fact that even the $x = 0$ compound has its chemical potential in the bottom of the conduction band, a closing of the band gap should increase the absorption as the low energy joint density of states increases. Therefore, we conclude that in this set of samples a topological phase transition occurs by closing and reopening of the bandgap in the range of x=0.05 - 0.06. These changes of the band structure on large energy scales accompany a transition in the topological class. Therefore, we associate the sudden collapse in the transport lifetime with a loss of topological protection of the surface states upon entering the non-topological state. Our results show directly how the robust transport properties and topological protection of the surface states are dependent on bulk band inversion. Note that the spectral weight of Drude component also changes as a function of indium substitution (Fig. 3(b)). The origin of the change is unclear, but may arise in a shift of spectral weight from higher energies or a change in the surface state Fermi velocity.

It may be significant that we observe the threshold for increased scattering rate at $x = 0.05$, while the MIR absorption peaks (and presumably the band gap closes and the topolog-

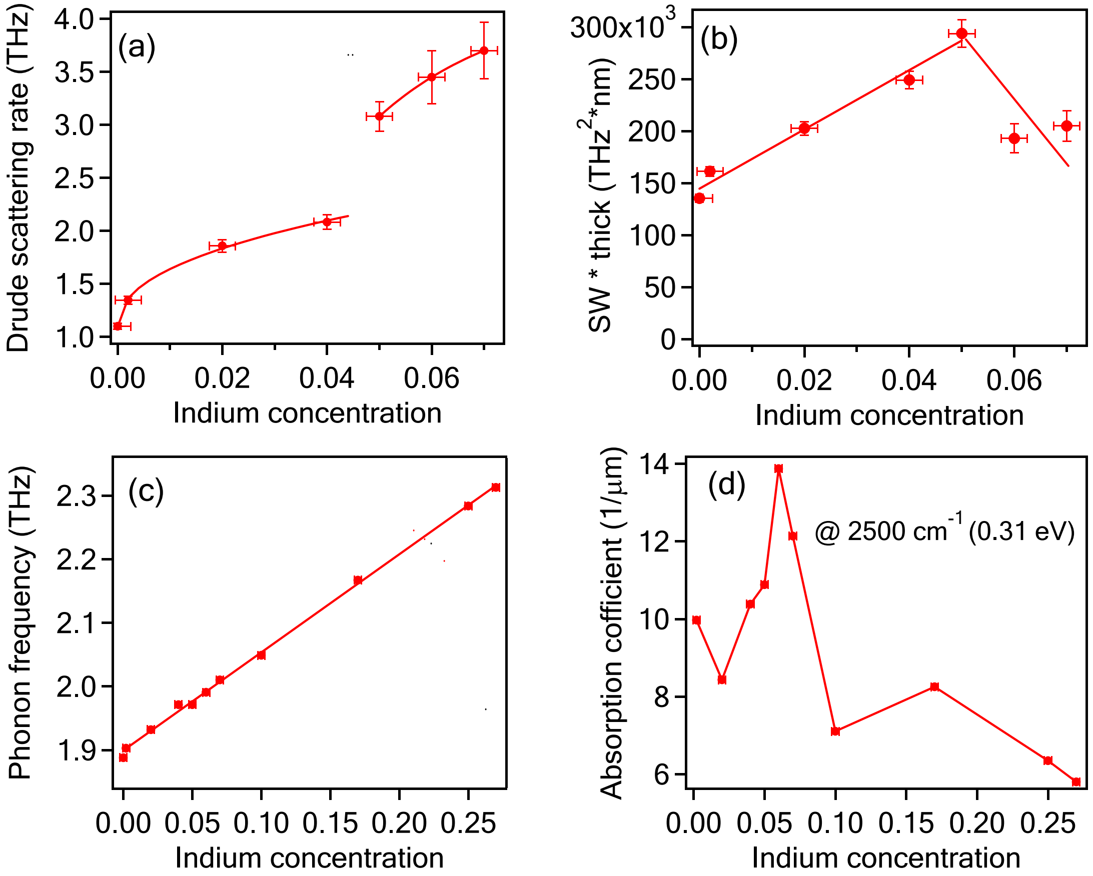

FIG. 3: (Color online) (a) Scattering rate of Drude term from Drude-Lorentz fits as a function of indium substitution. Solid lines are guidance to the eye. (b) Spectral weight (ω_p^2) * thickness as function of indium concentration. Solid lines are guidance to the eye. (c) α mode phonon frequency shift. The solid line is a linear fit. (d) Room temperature mid-infrared absorption coefficient at 0.31 eV (2500 cm^{-1}) as a function of indium concentration.

ical class changes) at $x = 0.06$. The small difference could be related to the finite thickness of the film. In general one expects that the penetration length of the topological wave function is proportional to $\hbar v_F/\Delta$. Hybridization of the two surfaces may be possible when this length scale is of order half the film thickness. If the surface state is of order a few nm deep at $x = 0$, a simple estimate based on linearly extrapolating its 0.35 eV band gap to close at $x = 0.06$, shows that a 64 QL film could easily have the threshold for the two topological surface state to hybridize and thus increased scattering shifted downward by $x = 0.01$. A natural consequence of this idea is that the substitution level of this threshold should have a strong thickness dependence for thin films, but a weaker one for thick films.

It is interesting to note that in the present system the topological phase transition appears to occur at rather low substitutions, while in the previously studied class of $\mathrm{TlBi(S_{1-x}Se_x)_2}$ the transition occurred near $x = 0.5$. This difference may be due to the extreme sensitivity of substitutions of bismuth by the light element indium and therefore strongly suppressed SO coupling, or to the particulars of the fact that the nominal electron configuration of indium is 5s^2 5p^1 while bismuth is 6s^{2}6p^3. Interestingly, the unusual mass acquisition away from the topological transition in the $\mathrm{TlBi(S_{1-x}Se_x)_2}$[12] may also be observed in the present case as ARPES measurements on $\mathrm{(Bi_{1-x}In_x)_2Se_3}$ have shown that a gap opens up at the Dirac point for $x = 0.03$,[13] while the scattering rate and DC transport does not change dramatically until higher substitutions.[23] The latter doping range is in the region where the peak in the MIR absorption occurs, which we may associate with the bulk band gap closing and the topological class changing.

Note that in this study, we have not ascribed any of the conductance changes with doping to explicitly bulk spectral features. In this regard, we believe that the very strong dependence of the band gap with doping presumably makes the $\mathrm{(Bi_{1-x}In_x)_2Se_3}$ a challenging system to observe *bulk* fermionic criticality in [24]. Linear extrapolating the band gap to zero at $x = 0.06$ means that even a 1% difference in doping changes the band gap by ≈ 55 meV, which is a value well in excess of the THz photon energy.

In conclusion, we have studied the quantum phase transition between topological and non-topological states in the $(Bi_{1-x}In_x)_2Se_3$ series. The low frequency Drude peak that we have previously shown to be associated with topological surface transport shows only small broadening at low indium substitutions. Around $x = 0.05$, the width of the Drude peak drastically increases showing a large decrease in the transport lifetime. We can correlate these changes with a peak in the MIR absorption in this substitution range that indicates the closing and inversion the bulk band gap and a transition in topological class. We therefore associate increase in scattering of the surface state with the loss of topological protection. We hope this work can generate further interest in this topological phase transition, particularly first principle calculations for In substitution in Bi_2Se_3 to reveal the evolution of the bulk band structure, such as gap closing and band inversion.

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